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INFORMATION TRACES DISCLOSURE STATEMENT BY APPLICANT						ATTY. DOCKET NO. F064			SERIAL NO. 09/765,806		
						FILING	DATE		GRO	OUP ART	UNIT
APPLICANT	s Gei	nacn	et al.			January 19, 2001			2881		
				· U.S. PATE	NT DOCUMENTS						
*Examiner Initial	Cite No.	Patent Number		Issue Date	Patentee		Class	Subo	Subclass		Date (if opriate)
YM &	A	4,6	34,871	Jan 6 1987	Knauer		250	398	398		
m.E.	В	4,6	61,709	Apr 28, 1987	Walker		250	492	492.2		
ME	С	4,6	94,178	Sep 15, 1987	Harte		250	396	396		
M.E.	D	4,8	76,112	Oct 24, 1989	Kaito et al.		427	38	38		. 7
-3.m	Е	5,0	51,556	Sep 24, 1991	Sakamoto		219	121	121.25) (°
M.E.	F	5,1	88,705	Feb 23, 1993	Swanson		156	643	643		<u> </u>
ME.	G	5,4	35,850	Jul 25, 1995	Rasmussen		118	726	726		£
M,E.	Н	5,8	27,786	Oct 27, 1998	Puretz		438	789	789		
W.E.	Ι	5,9	45,677	Aug 31,1999	Leung		250	396	396		
M.E.	J	6,0	11,269	Jan 4, 2000	Veneklasen		250	492	2.23		
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	Docume		Date	Country		Class		Subclass		Translat	ion
	Numb	CI								Yes	No
			(INCLU	OTHER IDING AUTHOR, TITL	R DOCUMENTS LE, DATE, PERTINE	NT PAGI	ES, ETC.)				
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ME.	К	ΙE	BAUER, E., Koziol, C., Lilienkamp, G., Schmidt, T., "Spectromicroscopy in a Low Energy Electron Microscope," <i>Journal of Electron Spectroscopy and Related Phenomena</i> 84 (1997) pp 201-209								
M.E.	L	S	EDINGER, KLAUS AND KRAUS, THOMAS, "Modeling of Focused Ion Beam Induced Surface Chemistry," <i>Journal of Vacuum Science Technology</i> B 18(6), Nov/Dec 2000; pp 3190-3193.								
M.E	М		LEE, Y., et al. "Development of Ion Sources for Ion Projection Lithography" Journal of Vacuum Science Technology, B 14(6), Nov/Dec 1996; pp 3947-3950.								

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mæ.	0	ORLOFF, J., and SWANSON, L. W., "Some Considerations on the Design of a Field Emission Gun for a Shaped Spit Lithography System," <i>Optik</i> , Vol. 61, No.3 (1982), pp 237-245.					
ME.	P	ORLOFF, J., and SUDRAUD, Pierre, "Design of a 100 kV, High Resolution Focused Ion Beam Column with a Liquid Metal Ion Source" Microelectronic Engineering 3 (1985)pp. 161-165					
ME.	Q	SATO, M., and ORLOFF, J. "A Method for calculating the Current Density of Charged Particle Beams and the Effect of Finite Source Size and Spherical and Chromatic Aberrations on the Focusing Characteristics," <i>Journal of Vacuum Science Technology</i> , B, Vol 9, No. 5, Sep/Oct 1991; pp 2602-2608					
M .E.	STICKEL, W., "Simulation of Columb Interactions in Electron Beam Lithography Systems-A Comparison of Theoretical Models," Papers from the 42 nd International Conference on Electron, Ion, and Photon Beam Technology and Nanofabrication, 26-29 May 1998.						
M.E.	S	SLINGERLAND, H. N., "Optimization of a Chromatically Limited Ion Microprobe," Microelectronic Engineering 2 (1984) 219-226					
M.E.	Т	TUGGLE, D.W., SWANSON, L.W., and GESLEY, M. A., "Current Density Distribution in a Chromatically Limited Electron Microprobe", J. Vac. Sci. Technol. B4 (1) Jan/Feb 1986 pp. 131-134					
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^{*}EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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m.9	î.	A	4,609,809)	02 Sep 8	36	Yamaguchi		219	121	121EM	
W.8	. •	В	4,820,89	3	11 Apl 8	39	Slingerland		219	121.12		
M.E	<i>,</i> .	С	4,874,460)	17 Oct 8	39	Nakagawa		156	626		
M.8	<u>, </u>	D	4,894,549	9	16 Jan 9	0	Stengl		250	492.2		
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											Yes No	
M.E	D	E391	0054A1 1		1Oct 90 Germany			H01J37 30)		
Mr.	Е	P0257	7685B1 09		Jan 91	European Patent Office			H01J 37	7 317		
YM.E.	J	JA6169125 09		09	Apl 86 Japan - Abstract			H01J37 30)5		
M.E	WO0075954 1		14	Dec 00	WIPO			H01J37 31		.7		
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YM .{	E HAWKES, P.W. and KASPER, E., <u>Principles of Electron Optics</u> , Vol. 2., Applied Geometrical Optics, Academic Press, 1989: Chapters 47, 48. Pp971-1003.											
M.8	<u>.</u>	F	http://v	"Plasma Ion Source-ECR microwave plasma ion source," http://www.tectra.de/plasma-ion-source.htm, Feb 18, 2000 Contact: Dr. Christian Bradley, tectra GmbH, Reuterweg 65, D-60323 Frankfurt/M.								
M.	€.	G	MAST Microc	SLINGERLAND, H.N., BARTH, J.E., KOETS, E. KRAMER, J. van der MAST, K.D., "Proposal for a Second Generation IBPG," Proceedings Microcircuit Engineering Conference, 1984, <i>Microcircuit Engineering</i> , 1985, pp. 381-387								

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M.G.	I _.	Van der MAST, K.D., JANSEN, G.H., BARTH, J.E., "The Shower-Beam Concept" <i>Microelectronic Engineering 3</i> (1985), Elsevier Science Publishers B.V. (North Holland), pp 43-51.						
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M.E.	K	VIJGEN, L., "Coulomb Interactions in Focused Ion Beam Columns," 3 Beams Conference 1992.						
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Sheet 1 of 1 ATTY. DOCKET NO. SERIAL NO. **INFORMATION** F064 09/765,806 **DISCLOSURE STAT** BY APPLICANT GROUP ART UNIT FILING DATE APPLICANTS Gerlach et al. January 19, 2001 2881 **U.S. PATENT DOCUMENTS** Class Subclass Filing Date (if Patent Number Issue Date Patentee *Examiner Cite appropriate) Initial No. UM & 250 310 5,093,572 Mar 3, 1992 Hosono Α ME 492.2 В Sept 22, 1992 250 5,149,974 Kirch, et al. M & 309 \mathbf{C} 5,376,791 Dec 27, 1994 Swanson et al. 250 ME D 5,574,280 Nov 12, 1996 Fujii et al. 250 309 FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION Examiner Cite Document Number Date Country Class Sub-class Translation Initial Yes Ε EP 0 927 880 A1 H01J37 20 M.E 21 July 98 European yes Patent Office **OTHER DOCUMENTS** (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) *Examiner Cite . Initial No. EDINGER, Klaus, YUN, Victor, MELNGAILLIS, John and ORLOFF, Jon, W.E. "Development of a High Brightness Gas Field Ion Source," J. Vac. Sci. Technol. B(6), Nov/Dec 1997, pp. 2365-2368 F GUHARAY, S.K., WANG, W., DUDNIKOV, V.G., REISER, M. ORLOFF, J. And MEINGAILLIS, J., "High-brightness Ion Source for Ion M.G.

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